ABSTRACT

WAFER PROCESSING METHOD

A wafer processing method for dividing a wafer into individual device chips along a plurality of scheduled division lines includes a protective film forming step of coating liquid-state resin, which is hardened by irradiation of ultraviolet rays thereon, on the front face of the wafer to form a protective film, a protective film hardening step of irradiating ultraviolet rays upon the protective film to harden the protective film, a protective tape adhering step of adhering a protective tape on a front face of the hardened protective film, a modified layer forming step of irradiating a laser beam of a wavelength having a transparency to the wafer along the scheduled division lines with a focal point thereof positioned in the inside of the wafer to form a modified layer along the scheduled division lines in the inside of the wafer, and a back face grinding step of grinding, a back face of the wafer while grinding water is supplied to thin the wafer to a given thickness and divide the wafer into the individual device chips along the scheduled division lines using the modified layer as a start point of the break.

(Figure 10)